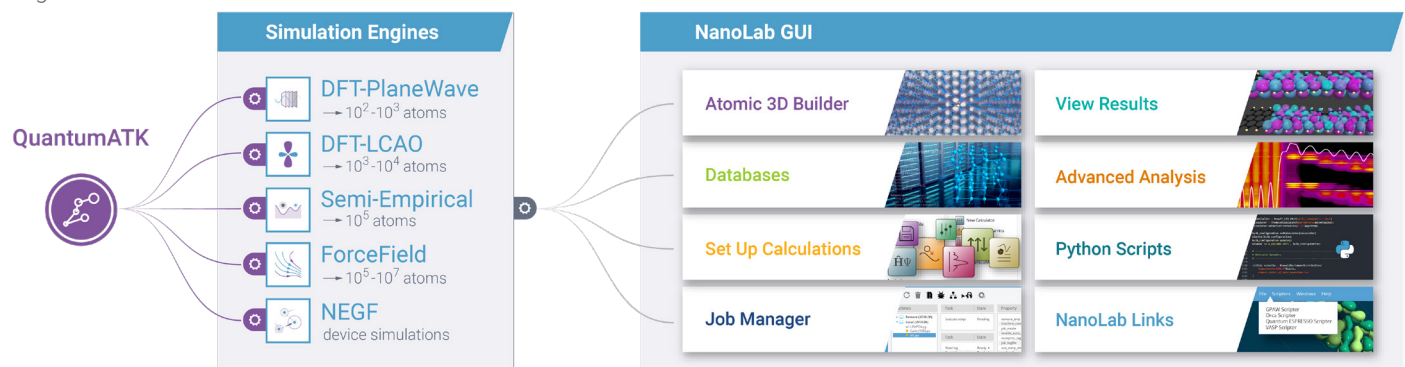


# QuantumATK-M Simulation Engines for Materials Development

QuantumATK-M is a complete and fully integrated software suite for atomic-scale modeling of materials, professionally engineered using state-of-the-art scientific and software-engineering methods. It combines the power of a Python scripting engine with the ease-of-use provided by an intuitive NanoLab graphical user interface (GUI). All simulation engines share a common infrastructure for analysis, ion dynamics, and parallel performance techniques. This datasheet describes QuantumATK-M simulation engines. You can download another datasheet on the NanoLab GUI.



## Core Features of QuantumATK-M

### NEGF Method for Nanoscale Device and Transport Simulations

Non-Equilibrium Green's function (NEGF) module works with DFT-LCAO, Semiempirical and ForceField Modules (see next page)

- ▶ **Types of Systems:** Nanoelectronic Devices & Interfaces (2-Probe), Surfaces (1-Probe, beyond slab approximation)
- ▶ **Include:**
  - Surface, defect, interface, grain boundary scattering, and charge transfer effects
  - External electric fields
  - An effective doping scheme to simulate doped semiconductors
  - Metallic gate electrodes, dielectric screening regions and implicit solvent models
  - Electron-phonon coupling (EPC) effects (MD-Landauer, STD-Landauer methods, and inelastic transmission methods)
  - Relaxation of device geometries
  - Multilevel parallelism up to 1000s of cores
  - Options to balance performance vs. memory usage
- ▶ **Calculate:**
  - Band-alignment, Schottky barriers, and work functions for thin-film/surface heterostructures
  - Electronic surface states in external electric fields
  - Insight into catalytic activity of transition metal and transition metal oxide surfaces
  - Thermal conductance/conductivity of materials, nanostructures, interfaces, etc.
  - Electrical characteristics, such as I-V curves, on/off ratio, subthreshold slope, drain-source saturation voltage, drain-induced barrier lowering, transconductance
  - Transmission spectrum, eigenvalues, eigenchannels, device density of states (DOS), etc
  - Phonon-limited mobility and resistivity of materials
  - Tunnel magnetoresistance ratio, spin-polarized tunneling current, and bias-dependent spin-transfer torque for material stacks that comprise the magnetic tunnel junctions
  - Photocurrent and open circuit voltage for solar-cell devices and LEDs

## Core Features of QuantumATK-M

- **DFT-LCAO:** Simulation engine for density functional theory (DFT) using pseudo-potentials and linear combinations of atomic orbitals (LCAO) basis sets.
- **DFT-PlaneWave:** Simulation engine for DFT using pseudo-potentials and plane-wave basis sets.
- **SemiEmpirical:** Semi-empirical simulation engine for using DFTB, extended Hückel, Slater-Koster, and other tight-binding models.
- **ForceField:** Simulation engine for atomic-scale simulations (e.g. molecular dynamics (MD)) using classical potentials.

**DFT-PlaneWave**  
↑ 10<sup>2</sup>-10<sup>3</sup> Atoms

**DFT-LCAO**  
↑ 10<sup>3</sup>-10<sup>4</sup> Atoms

**SemiEmpirical**  
↑ 10<sup>5</sup> Atoms

**ForceField**  
↑ 10<sup>5</sup>-10<sup>7</sup> Atoms

|  | DFT-PlaneWave | DFT-LCAO | SemiEmpirical | ForceField |
|--|---------------|----------|---------------|------------|
| ▶ <b>Types of Systems:</b> Molecules, (poly)crystals, polymers, nanostructures, nanoparticles, alloys  | •             | •        | •             | •          |
| ▶ Works with NEGF method for simulations of nanoelectronic devices, interfaces, surfaces, solar-cells  |               | •        | •             | •          |
| ▶ <b>Use:</b> More than 300 LDA/GGA/MetaGGA DFT functionals  | •             | •        |               |            |
| ▶ Hybrid functionals using the ACE approximation   | •             |          |               |            |
| ▶ Van der Waals models: DFT-D2 and DFT-D3  |               | •        |               |            |
| ▶ Hubbard U term for LDA and GGA   |               | •        |               |            |
| ▶ Methods for accurate band gap calculations of semiconductors and insulators  | •             | •        |               |            |
| ▶ Norm-conserving Troullier-Martins PPs (FHI, SG15/PseudoDojo)   | •             | •        |               |            |
| ▶ Projector-augmented wave (PAW) PP method (beta)  | •             |          |               |            |
| ▶ Predefined numerical atomic orbital basis sets for different accuracy levels   |               | •        |               |            |
| ▶ Plane wave basis sets with automatic default cut-offs  | •             |          |               |            |
| ▶ Spin settings: unpolarized, polarized, noncolinear, noncollinear spin-orbit  | •             | •        | •             |            |
| ▶ Built-in Slater-Koster models for group IV and III-V semiconductors, extended Hückel model with over 300 basis sets, and Tight-Binding models for strained systems                   |               |          | •             |            |
| ▶ More than 300 empirical classical potentials included, Python interface for adding your own or literature potential, support for custom combination of potentials                    |               |          |               | •          |
| ▶ Gates, dielectric regions or implicit solvent models in devices or periodic structures   |               | •        | •             |            |
| ▶ <b>Perform:</b> Calculations of band structure, fat band structure, (P)DOS, Fermi surface, and many more   | •             | •        | •             |            |
| ▶ Boltzmann transport calculations of conductivity/mobility tensor, Hall coefficient and Hall conductivity tensor, Seebeck coefficient and ZT including electron-phonon coupling (EPC) |               | •        | •             |            |
| ▶ Geometry and unit cell optimization using LBFGS and FIRE methods   | •             | •        | •             | •          |
| ▶ Molecular dynamics (NPT, NVT, NVE, ...) simulations for studying mechanical (e.g. creep simulation), thermal properties, and physical processes (e.g. thin film growth)              | •             | •        | •             | •          |
| ▶ Time-stamped force-bias Monte Carlo simulations as an alternative to MD for long time-scale equilibration, deposition, amorphization, diffusion, sampling of rare events             | •             | •        | •             | •          |
| ▶ Nudged elastic band (NEB) for reaction path optimization (e.g. to get insight into catalytic activity of transition metal and transition metal oxide surfaces)                       | •             | •        | •             | •          |
| ▶ Adaptive kinetic Monte Carlo (AKMC) for long timescale kinetics (e.g. diffusion kinetics)  | •             | •        | •             | •          |
| ▶ Phonon modes (part of the STD-Landauer method to include EPC effects), phonon bandstructure, DOS, and thermal transport simulations  | •             | •        | •             | •          |
| ▶ <b>Benefit from:</b> Multilevel parallelism (threading + MPI) up to 1000s of cores. Parallelize over k-points/basis functions/NEB images/AKMC searches/bias points, etc.             | •             | •        | •             | •          |



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